^{110}Cd(p,p),(p,p′) IAR 1977So10

Type	Author	History Citation	Literature Cutoff Date
Full Evaluation	Jean Blachot	NDS 110, 1239 (2009)	1-Feb-2008

Others: 1969Ab09, 1970Ab02, 1970Mi08.
E(p)=5.8-8.1 MeV; resolution of excit 10-12 keV (semi).
Res parameters determined from theoretical fits to excit: Γ, Γ(p), mixing phase.

^{111}In Levels

E(level)[†]	L[‡]	S[&]	Comments
11772	0	0.59	IAS of 1/2$^+$ ^{111}Cd g.s..
12036	2[@]	0.11	IAS of 254-keV, 5/2$^+$ ^{111}Cd excitation.
12142			IAS is associated with 342-keV, 3/2 *2* 0.036 C.
12403	2[#]	0.42	IAS is associated with 620-keV, 5/2$^+$ ^{111}Cd excitation.
12503	2[@]	0.029	Possible IAS of 736-keV, L=2 (p,p′) ^{111}Cd excitation.
12640	2[#]	0.29	Possible IAS of 866.7-keV, 3/2$^+$ ^{111}Cd excitation.
12826	0	0.14	IAS is associated with 1020-keV, 1/2$^+$ ^{111}Cd excitation.
12965	0	0.044	IAS is associated with 1190-keV, 1/2$^+$ ^{111}Cd excitation.
13100	0	0.077	IAS may be associated with 1330-keV level in ^{111}Cd.

[†] From S(p)=5332 *5* (2003Au03 + res E(p)(C.M.).
[‡] Deduced from angular distributions compared with quasiparticle random-phase approximation.
[#] 3/2$^+$ for L=2 resonance from excit, angular distribution.
[@] 5/2$^+$ assigned to L=2 resonances.
[&] Spectroscopic factor extracted from elastic analog res scattering data.